Product data sheet

1. Product profile

1.1 General description

Ultrafast, dual common cathode, epitaxial rectifier diode in a SOT78 (TO-220AB) plastic package.

1.2 Features

- Fast switching
- Soft recovery characteristic
- Low switching loss

- Low thermal resistance
- Low forward voltage drop
- High thermal cycling performance

1.3 Applications

- Output rectifiers in high frequency switched-mode power supplies
- Discontinuous Current Mode (DCM)Power Factor Correction (PFC)

1.4 Quick reference data

- $V_{RRM} \le 600 \text{ V}$
- V_F ≤ 1.16 V

- $I_{O(AV)} \le 20 \text{ A}$
- $t_{rr} \le 60 \text{ ns}$

2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	anode 1		
2	cathode	mb	1
3	anode 2	7 9 5	2
mb	mounting base; cathode	1 2 3	sym084
		SOT78 (3-lead TO-220A	.B)

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3. Ordering information

Table 2. Ordering information

Type number	Package				
	Name	Description	Version		
BYV34-600	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78		

4. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

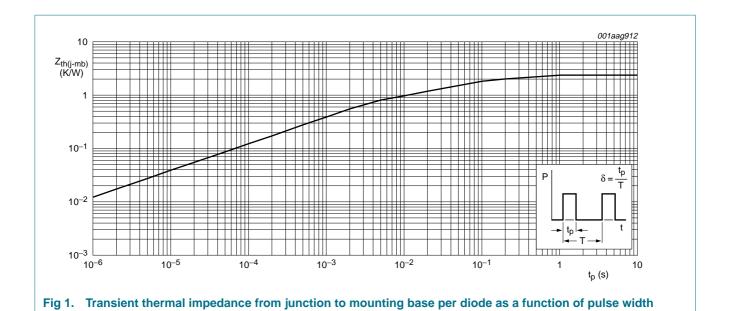
		,			
Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	square waveform; δ = 1.0; $T_{mb} \le 138 ^{\circ}C$	-	600	V
I _{O(AV)}	average output current	square waveform; δ = 0.5; $T_{mb} \le 107$ °C; both diodes conducting	-	20	Α
I _{FRM}	repetitive peak forward current	t = 25 μ s; square waveform; δ = 0.5; $T_{mb} \le$ 107 °C; per diode	-	20	Α
I _{FSM}	non-repetitive peak forward current	t = 10 ms; sinusoidal waveform; per diode	-	120	Α
		t = 8.3 ms; sinusoidal waveform; per diode	-	132	Α
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	150	°C

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; per diode; see Figure 1	-	-	2.4	K/W
		with heatsink compound; both diodes conducting	-	-	1.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

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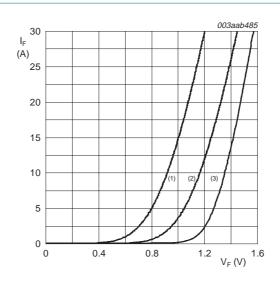
6. Characteristics

Table 5. Characteristics

 $T_i = 25 \,^{\circ}C$ unless otherwise specified.

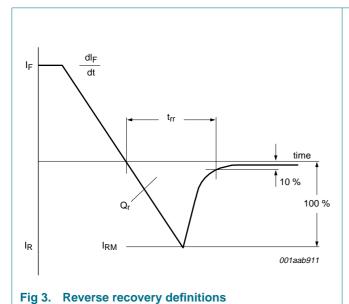
Parameter	Conditions	Min	Тур	Max	Unit	
Static characteristics						
forward voltage	$I_F = 10 \text{ A}; T_j = 150 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 2}}{}$	-	0.92	1.16	V	
	I _F = 20 A; see <u>Figure 2</u>	-	1.07	1.48	V	
reverse current	V _R = 600 V	-	10	50	μΑ	
	$V_R = 600 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	0.2	0.6	mA	
Dynamic characteristics						
recovered charge	I_F = 2 A to V_R \geq 30 V; dI_F/dt = 20 A/ μ s; see Figure 3	-	40	70	nC	
reverse recovery time	$I_F = 1 \text{ A to V}_R \ge 30 \text{ V};$ $dI_F/dt = 100 \text{ A/}\mu\text{s}; \text{ see } \frac{\text{Figure 3}}{}$	-	50	60	ns	
peak reverse recovery current	$I_F = 10 \text{ A to V}_R \ge 30 \text{ V};$ $dI_F/dt = 50 \text{ A/}\mu\text{s}; T_j = 100 ^\circ\text{C};$ see Figure 3	-	3	5	Α	
forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 10 \text{ A}/\mu\text{s}$; see Figure 4	-	3.2	-	V	
	racteristics forward voltage reverse current characteristics recovered charge reverse recovery time peak reverse recovery current forward recovery	$ \begin{array}{ll} \text{forward voltage} & I_F = 10 \text{ A; } T_j = 150 \text{ °C; see } \underline{\text{Figure 2}} \\ I_F = 20 \text{ A; see } \underline{\text{Figure 2}} \\ I_F = 20 \text{ A; see } \underline{\text{Figure 2}} \\ \hline \text{reverse current} & V_R = 600 \text{ V} \\ \hline V_R = 600 \text{ V; } T_j = 100 \text{ °C} \\ \hline \text{characteristics} \\ \hline \text{recovered charge} & I_F = 2 \text{ A to } V_R \geq 30 \text{ V; dI}_F/\text{dt} = 20 \text{ A/}\mu\text{s; see } \underline{\text{Figure 3}} \\ \hline \text{reverse recovery time} & I_F = 1 \text{ A to } V_R \geq 30 \text{ V; dI}_F/\text{dt} = 20 \text{ A/}\mu\text{s; see } \underline{\text{Figure 3}} \\ \hline \text{peak reverse recovery current} & I_F = 10 \text{ A to } V_R \geq 30 \text{ V; dI}_F/\text{dt} = 50 \text{ A/}\mu\text{s; } T_j = 100 \text{ °C; see } \underline{\text{Figure 3}} \\ \hline \text{forward recovery} & I_F = 10 \text{ A; dI}_F/\text{dt} = 10 \text{ A/}\mu\text{s;} \\ \hline \end{array} $	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	

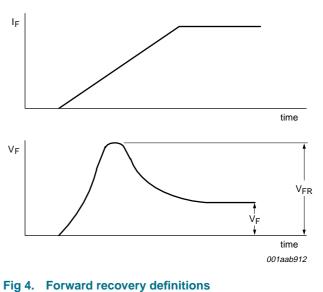
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- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values
- (2) $T_j = 150 \,^{\circ}\text{C}$; maximum values
- (3) $T_j = 25$ °C; maximum values

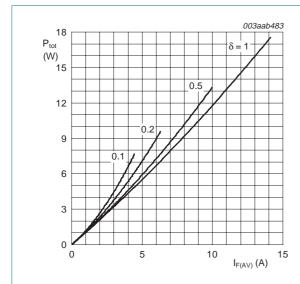
Fig 2. Forward current as a function of forward voltage





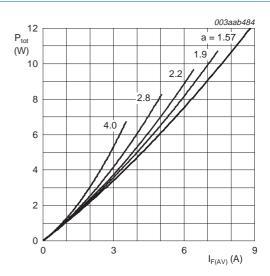
BYV34-600

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 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$

Fig 5. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



 $a = form factor = I_{F(RMS)} / I_{F(AV)}$

Fig 6. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

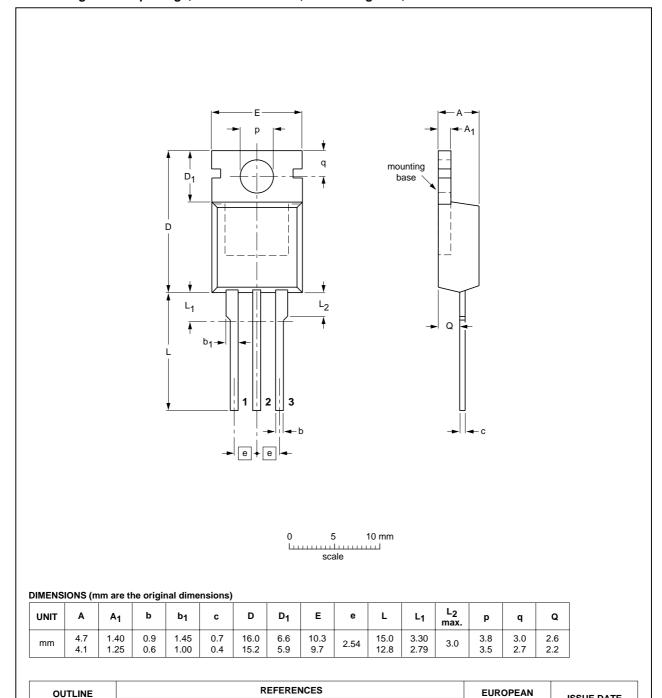


Fig 7. Package outline SOT78 (3-lead TO-220AB)

JEITA

SC-46

JEDEC

3-lead TO-220AB

ISSUE DATE

05-03-22

PROJECTION

VERSION

SOT78

Dual rectifier diode ultrafast

8. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV34-600 V.2	20180928	Product data sheet	-	BYV34-600_1
Modification:	Change from NXP version to WeEn Version			
BYV34-600_1	20071004	Product data sheet	-	-

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9. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина,

дом 2, корпус 4, литера А.